

Docket No.: 63979-032

PATENT

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Yoshiaki HASEGAWA, et al.

Serial No.: 10/643,944

Filed: August 20, 2003



: Customer Number: 20277

: Confirmation Number:

: Group Art Unit:

: Examiner:

For: SEMICONDUCTOR LASER AND PROCESS FOR MANUFACTURING THE SAME

INFORMATION DISCLOSURE STATEMENT

Mail-Stop IDS
Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In accordance with the provisions of 37 C.F.R. 1.56, 1.97 and 1.98, the attention of the Patent and Trademark Office is hereby directed to the references listed on the attached form PTO-1449. It is respectfully requested that the references be expressly considered during the prosecution of this application, and that the references be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

This Information Disclosure Statement is being filed within three months of the U.S. filing date OR before the mailing date of a first Office Action on the merits. No certification or fee is required.

Each non-English language reference was first cited in a corresponding foreign application search report or office action and its relevance discussed therein. A copy of the

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foreign search report or office action, together with an English language version thereof, is attached for the Examiner's information.

Please charge any shortage in fees due in connection with the filing of this paper, including extension of time fees, to Deposit Account 500417 and please credit any excess fees to such deposit account.

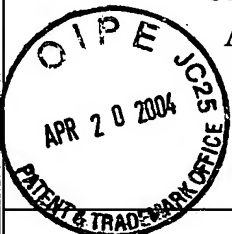
Respectfully submitted,

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INFORMATION DISCLOSURE CITATION IN AN APPLICATION  (PTO-1449)				ATTY. DOCKET NO. 63979-032		SERIAL NO. 10/643,944	
APPLICANT Yoshiaki HASEGAWA, et al.							
FILING DATE August 20, 2003						GROUP	
U.S. PATENT DOCUMENTS							
EXAMINER'S INITIALS	CITE NO.	Document Number Number-Kind Code2 (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear		
		US 5,345,463	09/06/1994	Mannoh et al.			
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EXAMINER'S INITIALS	CITE NO.	Foreign Patent Document Country Codes -Number 4 -Kind Codes (if known)	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines Where Relevant Figures Appear	Translation	
						Yes	No
		JP 10-200214 A	07/31/1998	NEC CORP			x
		JP 6-283825 A	10/07/1994	TOYODA GOSEI CO., LTD.			x
		JP 4-275479 A	10/01/1992	NEC CORP.			x
		JP 2000-21789	01/21/2000	TOSHIBA CORP.			x
		JP 5-291686	11/05/1993	-			x
		JP 11-251687	09/17/1999	-			x
OTHER ART (Including Author, Title, Date, Pertinent Pages, Etc.)							
EXAMINER'S INITIALS	CITE NO.	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.					
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		TOJYO, Tsuyoshi., et al. "GaN-Based High Power Blue-Violet Laser Diodes." The Japan Society for Applied Physics, Volume 40, Part 1. No. 5A, May 2001, pp.3206-3210					
		KURODA, Naotaka., et al. "Precise control of pn-junction profiles for GaN-based LD structures using GaN substrates with low dislocation densities." Journal of Crystal Growth 189/190 (1998) pp. 551-555					
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		BLAAUW, C., et al. "Secondary Ion mass spectrometry and electrical characterization of Zn diffusion in n-type InP." J. Appl. Phys. 66(2), July 15, 1989, American Institute of Physics, pp. 605610					
EXAMINER				DATE CONSIDERED			

*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

1 Applicant's unique citation designation number (optional). 2 Applicant is to place a check mark here if English language Translation is attached.